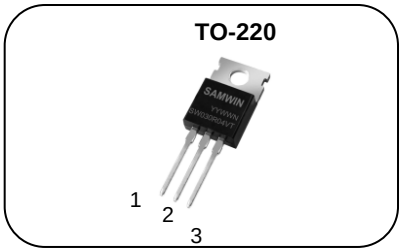
N-channel Enhanced mode TO-220 MOSFET

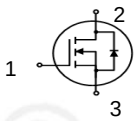
Features

- High ruggedness
- Low $R_{DS(ON)}$ (Typ 2.8mΩ)@V_{GS}=10V
  (Typ 3.7mΩ)@V_{GS}=4.5V
- Low Gate Charge (Typ 120nC)
- Improved dv/dt Capability
- 100% Avalanche Tested
- Application:Power Supply,LED Boost



1. Gate 2. Drain 3. Source

BV_{DSS} : 40V
I_D : 130A
$R_{DS(ON)}$: 2.8mΩ@V_{GS}=10V
3.7mΩ@V_{GS}=4.5V



General Description

This power MOSFET is produced with advanced technology of SAMWIN.
This technology enable the power MOSFET to have better characteristics, including fast switching time, low on resistance, low gate charge and especially excellent avalanche characteristics.

LEAD-FREE RoHS

Order Codes

Item	Sales Type	Marking	Package	Packaging
1	SW P 030R04VT	SW030R04VT	TO-220	TUBE

Absolute maximum ratings

Symbol	Parameter		Value	Unit
V_{DSS}	Drain to source voltage		40	V
I_D	Continuous drain current (@T_C=25°C)		130*	A
	Continuous drain current (@T_C=100°C)		82*	A
I_{DM}	Drain current pulsed	(note 1)	520	A
V_{GS}	Gate to source voltage		±20	V
E_{AS}	Single pulsed avalanche energy	(note 2)	826	mJ
E_{AR}	Repetitive avalanche energy	(note 1)	49	mJ
dv/dt	Peak diode recovery dv/dt	(note 3)	5	V/ns
P_D	Total power dissipation (@T_C=25°C)		121	W
	Derating factor above 25°C		0.98	W/°C
T_{STG}, T_J	Operating junction temperature & storage temperature		-55 ~ + 150	°C
T_L	Maximum lead temperature for soldering purpose, 1/8 from case for 5 seconds.		300	°C

*. Drain current is limited by junction temperature.

Thermal characteristics

Symbol	Parameter	Value	Unit
R_{thjc}	Thermal resistance, Junction to case	1.03	°C/W
R_{thja}	Thermal resistance, Junction to ambient	52	°C/W

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Electrical characteristic (T_C = 25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
Off characteristics						
BV_{DSS}	Drain to source breakdown voltage	V_{GS}=0V, I_D=250uA	40			V
ΔBV_{DSS} / ΔT_J	Breakdown voltage temperature coefficient	I_D=250uA, referenced to 25°C		0.02		V/°C
I_{DSS}	Drain to source leakage current	V_{DS}=40V, V_{GS}=0V			1	uA
		V_{DS}=32V, T_C=125°C			50	uA
I_{GSS}	Gate to source leakage current, forward	V_{GS}=20V, V_{DS}=0V			100	nA
	Gate to source leakage current, reverse	V_{GS}=-20V, V_{DS}=0V			-100	nA
On characteristics						
$V_{GS(TH)}$	Gate threshold voltage	V_{DS}=V_{GS}, I_D=250uA	1		3	V
$R_{DS(ON)}$	Drain to source on state resistance	V_{GS}=10V, I_D=130A		2.9	3.6	mΩ
		V_{GS}=10V, I_D=65A		2.8	3.5	mΩ
		V_{GS}=4.5V, I_D=65A		3.7	4.6	mΩ
G_{fs}	Forward transconductance	V_{DS}=10V, I_D=30A		140		S
Dynamic characteristics						
C_{iss}	Input capacitance	V_{GS}=0V, V_{DS}=20V, f=1MHz		5350		pF
C_{oss}	Output capacitance			686		
C_{rss}	Reverse transfer capacitance			644		
$t_{d(on)}$	Turn on delay time	V_{DS}=20V, I_D=30A, R_G=25Ω, V_{GS}=10V (note 4,5)		36		ns
t_r	Rising time			123		
$t_{d(off)}$	Turn off delay time			396		
t_f	Fall time			210		
Q_g	Total gate charge	V_{DS}=32V, V_{GS}=10V, I_D=30A (note 4,5)		120		nC
Q_{gs}	Gate-source charge			17		
Q_{gd}	Gate-drain charge			35		
R_g	Gate resistance	V_{DS}=0V, Scan F mode		1.3		Ω

Source to drain diode ratings characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_S	Continuous source current	Integral reverse p-n Junction diode in the MOSFET			130	A
I_{SM}	Pulsed source current				520	A
V_{SD}	Diode forward voltage drop.	I_S=30A, V_{GS}=0V			1.4	V
t_{rr}	Reverse recovery time	I_S=30A, V_{GS}=0V, dI_F/dt=100A/us		29		ns
Q_{rr}	Reverse recovery charge			19		nC

※. Notes
1. Repeatitive rating : pulse width limited by junction temperature.
2. L =1.84mH, I_{AS} =30A, V_{DD}=30V, R_G=25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 30A, di/dt = 100A/us, V_{DD} ≤ BV_{DSS}, Staring T_J =25°C
4. Pulse Test : Pulse Width ≤ 300us, duty cycle ≤ 2%.
5. Essentially independent of operating temperature.

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Fig. 1. On-state characteristics

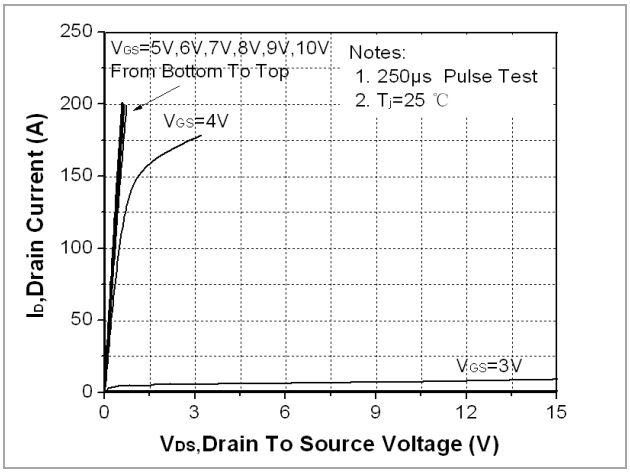


Fig. 2. On-resistance variation vs. drain current and gate voltage

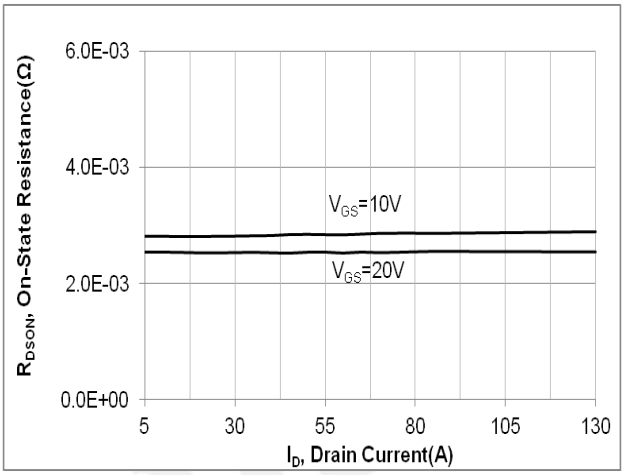


Fig. 3. Gate charge characteristics

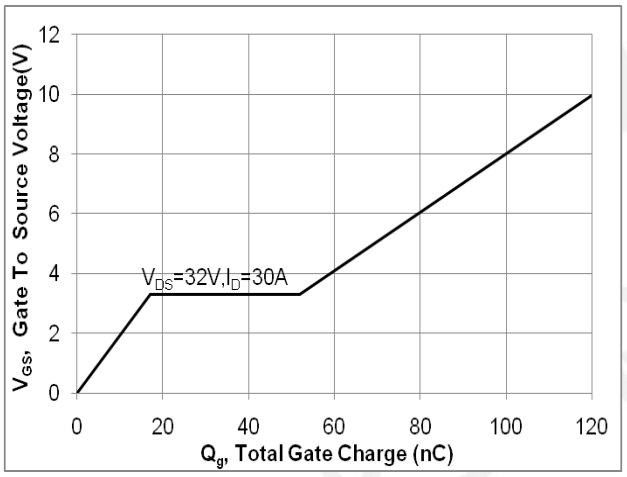


Fig. 4. On-state current vs. diode forward voltage

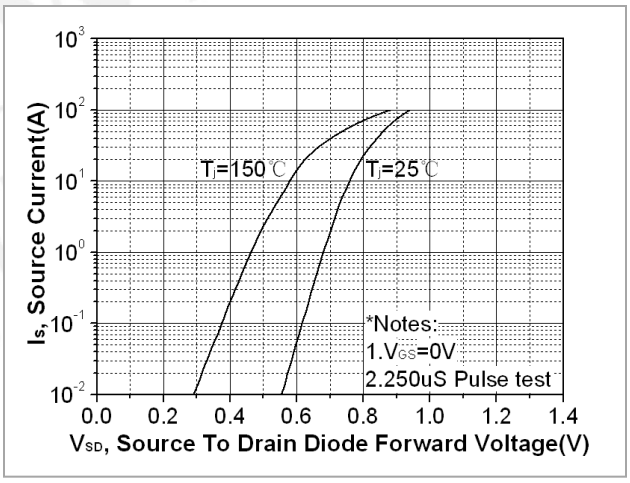


Fig 5. Breakdown voltage variation vs. junction temperature

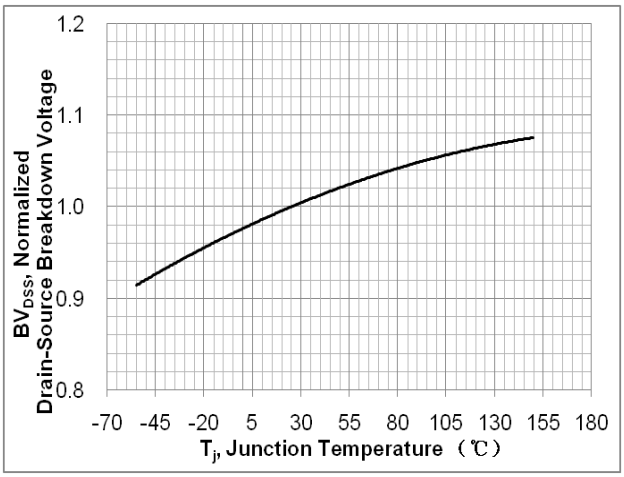
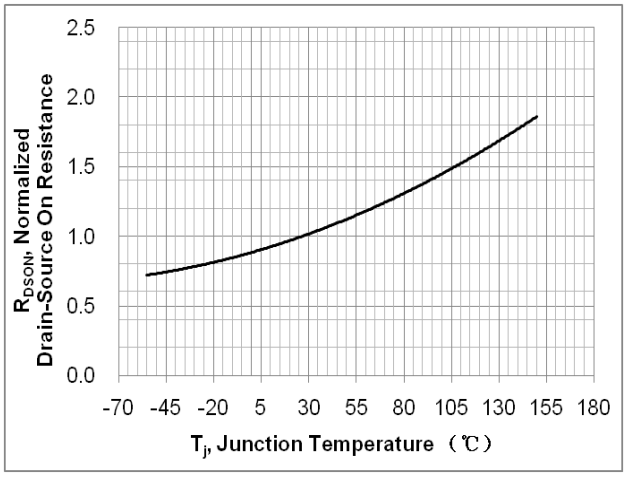


Fig. 6. On-resistance variation vs. junction temperature



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Fig. 7. Maximum safe operating area

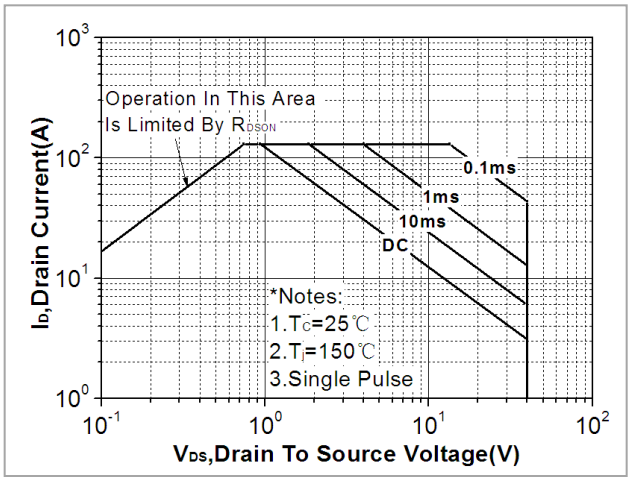


Fig. 8. Capacitance Characteristics

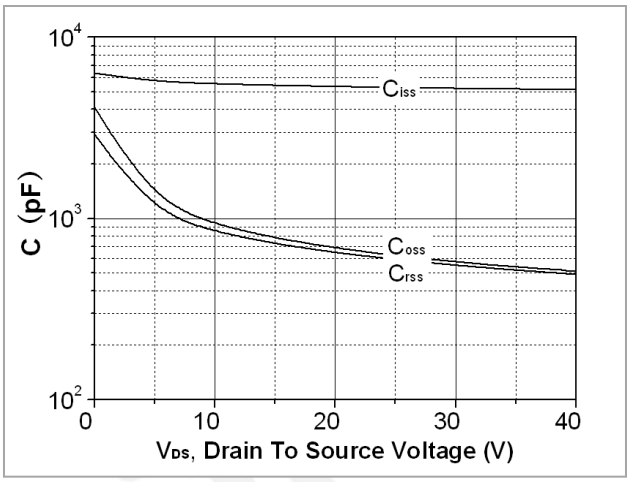


Fig. 9. Transient thermal response curve

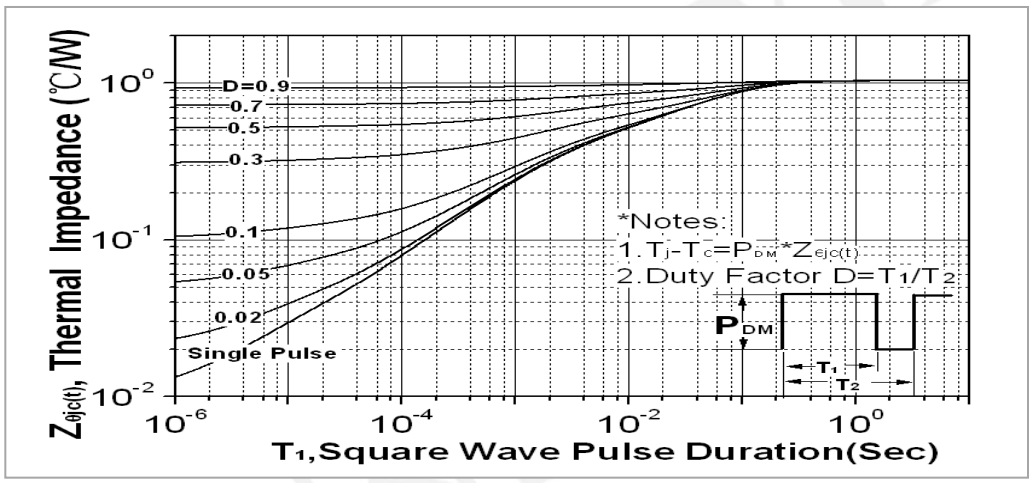
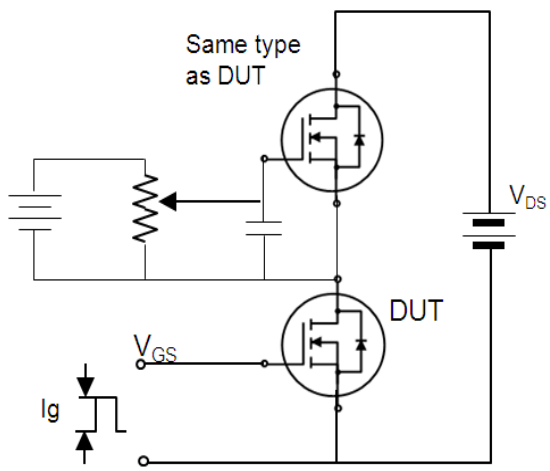
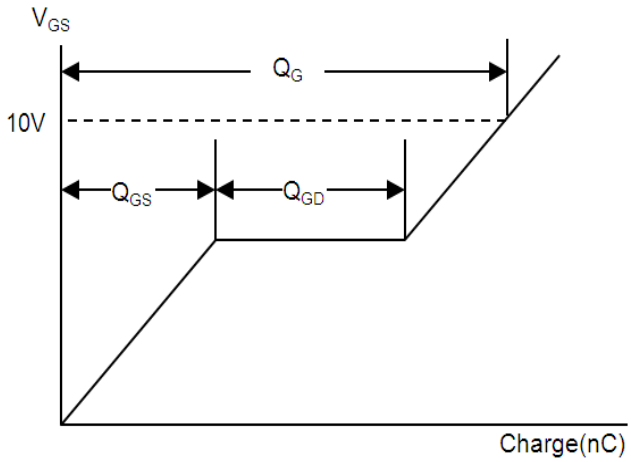


Fig. 10. Gate charge test circuit & waveform





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Fig. 11. Switching time test circuit & waveform

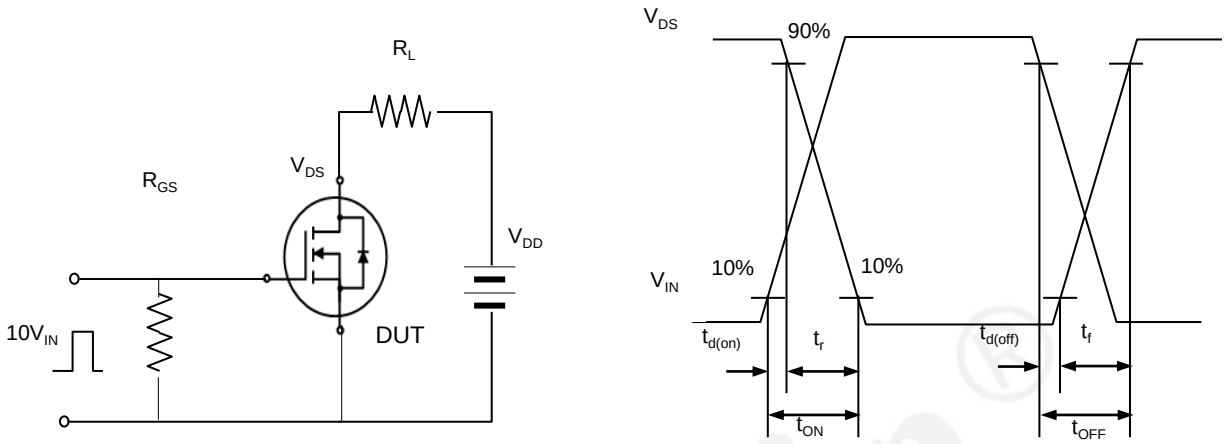


Fig. 12. Unclamped Inductive switching test circuit & waveform

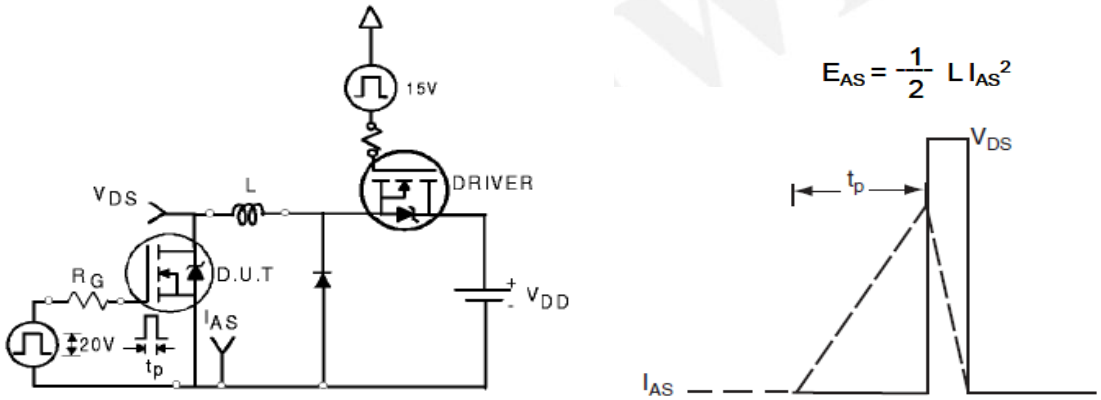
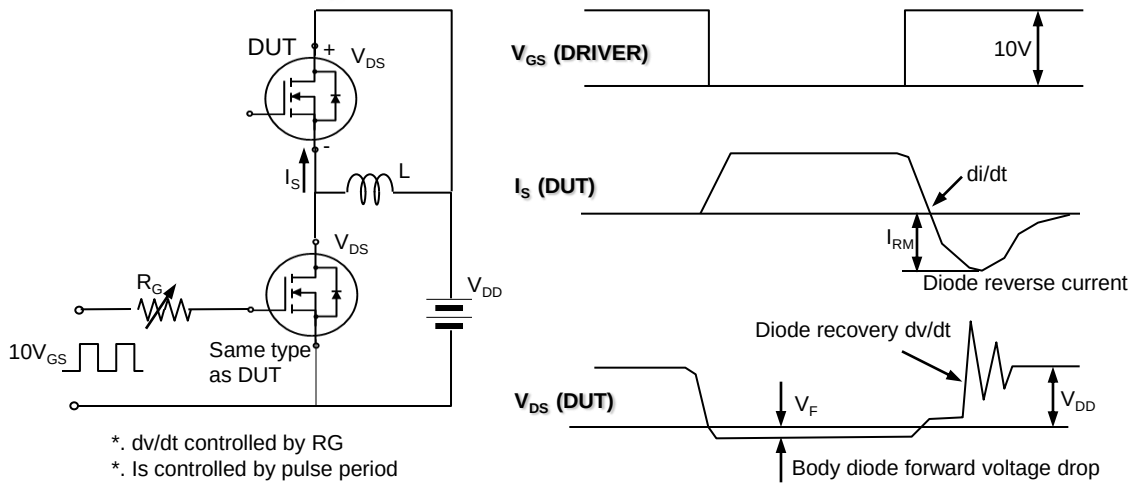


Fig. 13. Peak diode recovery dv/dt test circuit & waveform



*. dv/dt controlled by RG
*. Is controlled by pulse period

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